

# SQJQ960EL-T1\_GE3 Datasheet

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Man



DiGi Electronics Part Number	SQJQ960EL-T1_GE3-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	SQJQ960EL-T1_GE3
Description	MOSFET 2N-CH 60V 63A PPAK8X8
Detailed Description	Mosfet Array 60V 63A (Tc) 71W Surface Mount Pow erPAK® 8 x 8 Dual

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### Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SQJQ960EL-T1_GE3	Vishay Siliconix
Series:	Product Status:
TrenchFET*	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
	60V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ ld, Vgs:
63A (Tc)	9mOhm @ 10A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 250µA	24nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
1950pF @ 25V	71W
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
PowerPAK <sup>®</sup> 8 x 8 Dual	PowerPAK <sup>®</sup> 8 x 8 Dual
Base Product Number:	
SQJQ960	

### **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
ECCN:	HTSUS:
EAR99	8541.29.0095

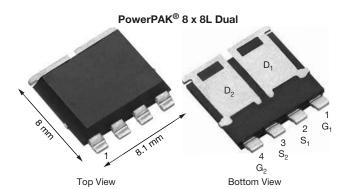


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# SQJQ960EL

**Vishay Siliconix** 

# Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET



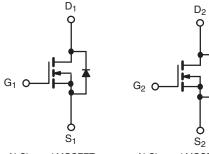
**PRODUCT SUMMARY** 60 V<sub>DS</sub> (V)  $R_{DS(on)}(\Omega)$  at  $V_{GS} = 10 V$ 0.009  $R_{DS(on)}$  ( $\Omega$ ) at  $V_{GS}$  = 4.5 V 0.013 63 I<sub>D</sub> (A) per leg Configuration Dual PowerPAK 8 x 8L Package

### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE



N-Channel MOSFET



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> :	= 25 °C, unles	s otherwise notec	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	60	V
Gate-source voltage		V <sub>GS</sub>	± 20	v
Continuous drain current	$T_C = 25 \ ^\circ C \ ^a$	Ŀ	63	
Continuous drain current	T <sub>C</sub> = 125 °C	۱ <sub>D</sub>	36	
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	50	А
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	200		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	26	
Single pulse avalanche energy		E <sub>AS</sub>	34	mJ
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P	71	W
Maximum power dissipation ~	T <sub>C</sub> = 125 °C	P <sub>D</sub>	24	٧V
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>d, e</sup>			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	75	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	2.1	C/W

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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### SQJQ960EL

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<b>SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C	, unless otherw	/ise noted)					
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static					•		
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	60	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	: 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	40	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0070	0.0090	
During a summer any state maniatement of		$V_{GS} = 4.5 V$	I <sub>D</sub> = 7 A	-	0.0092	0.0130	Ω
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0145	
		V <sub>GS</sub> = 10 V	l <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0180	
Forward transconductance b		V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	55	-	S
Dynamic <sup>b</sup>					•		•
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	1560	1950	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	771	964	
Reverse transfer capacitance	C <sub>rss</sub>			-	87	108	1
Total gate charge <sup>c</sup>	Qg			-	19	24	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, I_D = 10 \text{ A}$	-	4	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	2	-	
Gate resistance	Rg		f = 1 MHz		1.6	2.6	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	10	14	
Rise time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{DD}=30 \text{ V}, \text{ R}_L=4 \ \Omega \\ I_D\cong 10 \text{ A}, \text{ V}_{GEN}=10 \text{ V}, \text{ R}_g=1 \ \Omega \end{array}$		-	3	5	1
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	22	28	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	3	5	1
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>	•					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α
Forward voltage	V <sub>SD</sub>	IF	= 20 A, V <sub>GS</sub> = 0	-	1	1.2	V

Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

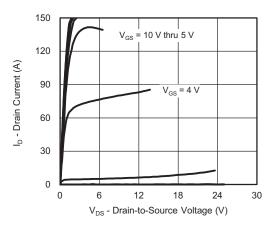
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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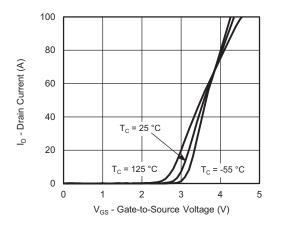


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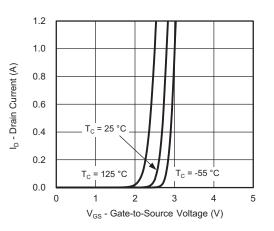
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



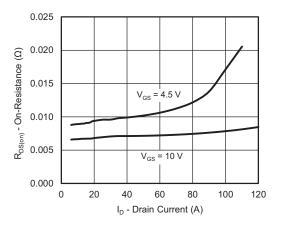
**Output Characteristics** 



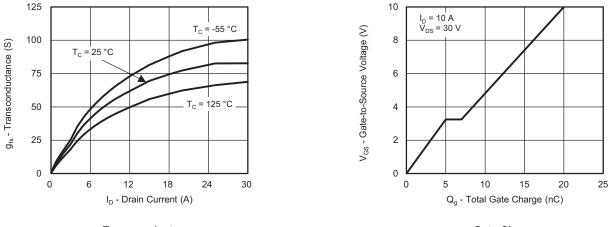
**Transfer Characteristics** 



**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 



Transconductance

Gate Charge

S17-0463-Rev. A, 27-Mar-17

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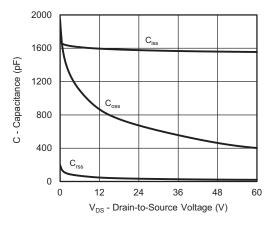
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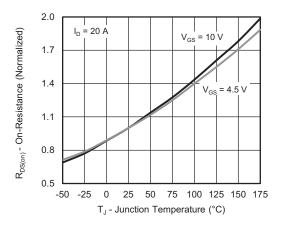


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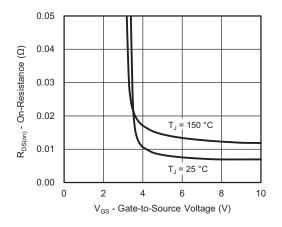
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



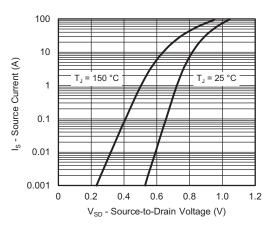
Capacitance



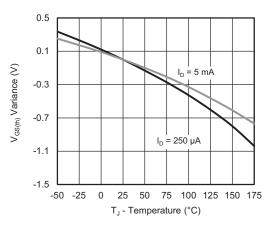
**On-Resistance vs. Junction Temperature** 



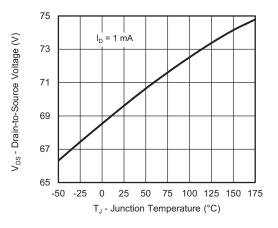
**On-Resistance vs. Gate-to-Source Voltage** 



Source Drain Diode Forward Voltage



**Threshold Voltage** 



Drain Source Breakdown vs. Junction Temperature

S17-0463-Rev. A, 27-Mar-17

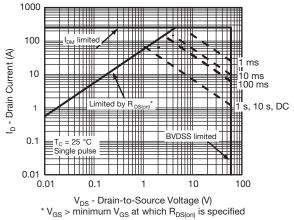
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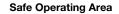
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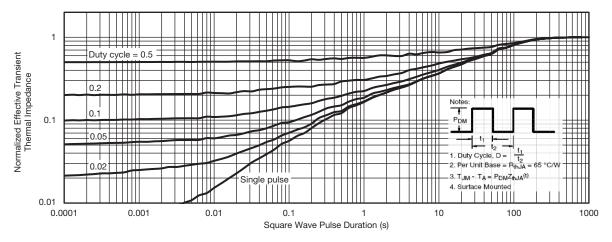


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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)







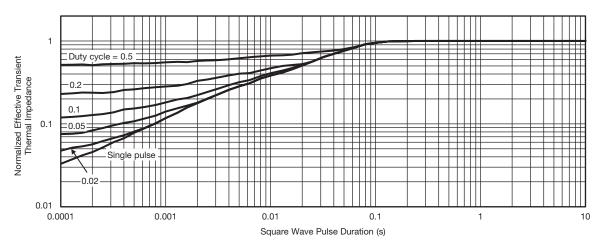
Normalized Thermal Transient Impedance, Junction-to-Ambient



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**THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

S17-0463-Rev. A, 27-Mar-17

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

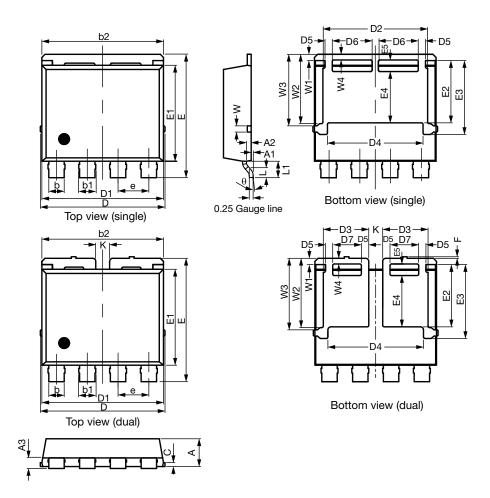
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## **Package Information**

**Vishay Siliconix** 

# PowerPAK<sup>®</sup> 8 x 8L Case Outline



DIM	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A2	0.25	0.30	0.35	0.010	0.012	0.014
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
С	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
D7	1.76	1.86	1.96	0.069	0.073	0.077

Revision: 16-Oct-17

Document Number: 67734

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# **Package Information**

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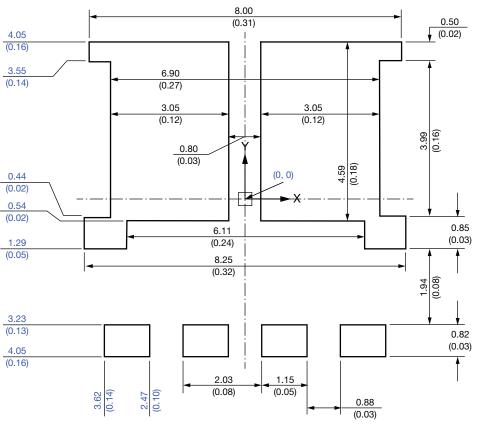
DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
E	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



### **PAD** Pattern

Vishay Siliconix

### **Recommended Minimum PADs for PowerPAK<sup>®</sup> 8 x 8L Dual**



Dimensions in millimeters (inches)

#### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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